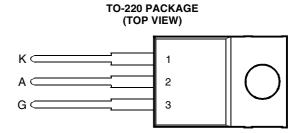
- 12 A Continuous On-State Current
- 100 A Surge-Current
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 20 mA



Pin 2 is in electrical contact with the mounting base.

MDC1ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIC126D		400		
Repetitive peak off-state voltage	TIC126M	V	600	V	
	TIC126S	V _{DRM}	700		
	TIC126N		800		
	TIC126D		400	٧	
Panatitiva nask ravarsa valtaga	TIC126M	V	600		
Repetitive peak reverse voltage	TIC126S	V _{RRM}	700		
	TIC126N		800		
Continuous on-state current at (or below) 70°C case temperature (see Note 1)			12	Α	
Average on-state current (180° conduction angle) at (or below) 70°C case temperature		1	7.5	Α	
(see Note 2)		I _{T(AV)}	7.5	^	
Surge on-state current at (or below) 25°C case temperature (see Note 3)		I _{TM}	100	Α	
Peak positive gate current (pulse width ≤ 300 μs)		I _{GM}	3	Α	
Peak gate power dissipation (pulse width ≤ 300 μs)		P _{GM}	5	W	
Average gate power dissipation (see Note 4)		$P_{G(AV)}$	1	W	
Operating case temperature range			-40 to +110	°C	
Storage temperature range		T _{stg}	-40 to +125	°C	
Lead temperature 1.6 mm from case for 10 seconds			230	°C	

NOTES: 1. These values apply for continuous dc operation with resistive load. Above 70°C derate linearly to zero at 110°C.

- 2. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 70°C derate linearly to zero at 110°C.
- 3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
- 4. This value applies for a maximum averaging time of 20 ms.



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST CONDITION	ONS	MIN	TYP	MAX	UNIT
I _{DRM}	Repetitive peak off-state current	V _D = rated V _{DRM}		T _C = 110°C			2	mA
I _{RRM}	Repetitive peak reverse current	V _R = rated V _{RRM}	I _G = 0	T _C = 110°C			2	mA
I _{GT}	Gate trigger current	V _{AA} = 12 V	$R_L = 100 \Omega$	t _{p(g)} ≥ 20 μs		8	20	mA
V _{GT} Gate trig		$V_{AA} = 12 \text{ V}$ $t_{p(g)} \ge 20 \mu\text{s}$	$R_L = 100 \Omega$	T _C = - 40°C			2.5	
	Gate trigger voltage	$V_{AA} = 12 \text{ V}$ $t_{p(g)} \ge 20 \mu\text{s}$	$R_L = 100 \Omega$			0.8	1.5	٧
		$V_{AA} = 12 \text{ V}$ $t_{p(g)} \ge 20 \mu\text{s}$	$R_L = 100 \Omega$	T _C = 110°C	0.2			
I _H F	Holding current	$V_{AA} = 12 \text{ V}$ Initiating I _T = 100 mA		T _C = - 40°C			100	mA
		$V_{AA} = 12 \text{ V}$ Initiating $I_T = 100 \text{ mA}$					40	
V_{T}	On-state voltage	I _T = 12 A	(see Note 5)				1.4	V
dv/dt	Critical rate of rise of off-state voltage	V _D = rated V _D	I _G = 0	T _C = 110°C		400		V/µs

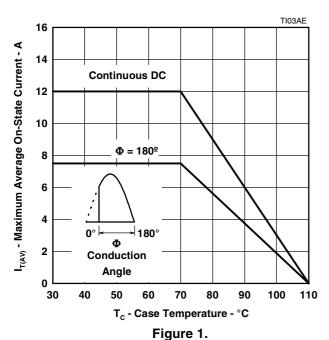
NOTE 5: This parameter must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2 \%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2.4	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

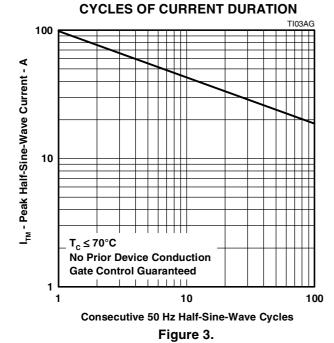
THERMAL INFORMATION

AVERAGE ON-STATE CURRENT DERATING CURVE



rigule i.

SURGE ON-STATE CURRENT vs



MAX ANODE POWER LOSS vs ON-STATE CURRENT

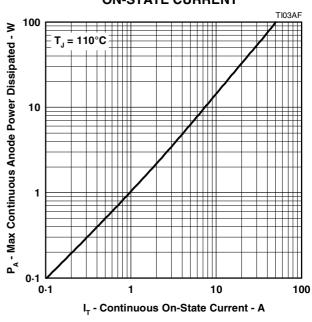


Figure 2.

TRANSIENT THERMAL RESISTANCE

CYCLES OF CURRENT DURATION

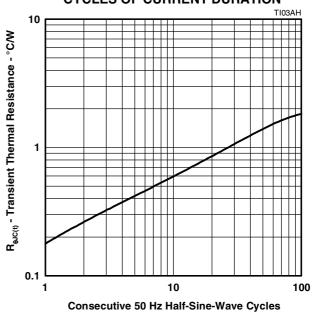
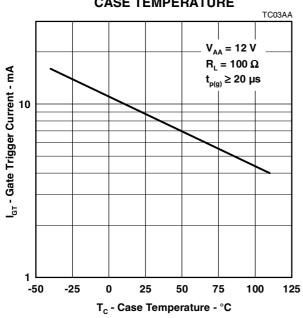


Figure 4.

TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT vs

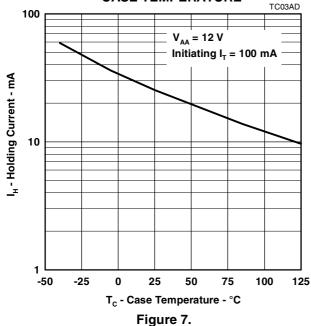
CASE TEMPERATURE



HOLDING CURRENT vs

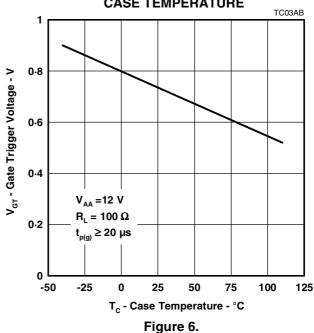
Figure 5.

CASE TEMPERATURE

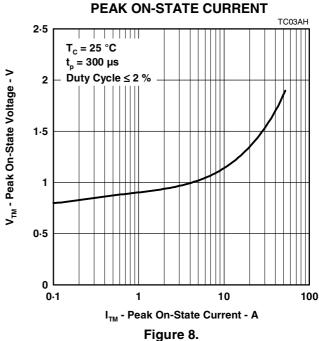


GATE TRIGGER VOLTAGE

CASE TEMPERATURE



PEAK ON-STATE VOLTAGE



Mouser Electronics

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Bourns:

TIC126D-S TIC126M-S TIC126N-S